

IN THE CLAIMS:

Claims 1-10 (Cancelled)

11. (Original) A method of selectively removing an oxide layer from a structure, said method comprising the steps of:

providing a semiconductor structure containing at least an oxide layer; and

selectively removing portions of said oxide layer utilizing a chemical oxide removal etch which is conducted in the presence of a plasma containing HF and NH₃.

12. (Original) The method of Claim 11 wherein said chemical oxide removal etch is performed at a pressure of about 6 millitorr or below.

13. (Original) The method of Claim 11 wherein said chemical oxide removal etch results in an undercut region being formed in said structure.

14. (Original) A low-resistance T-gate MOSFET comprising

a Si-containing substrate comprising at least one device channel/body implant region separating a source region from a drain region, said at least one device channel/body implant region having a length of less than about 0.1 μ m;

a gate dielectric located at least atop said device channel/body implant region, said source region and said drain region;

a T-gate located atop a portion of said gate dielectric, said T-gate comprises a recessed bottom polysilicon region and an upper gate conductor region, said upper gate conductor region has a width that is greater than a width of said bottom polysilicon region; and

nitride spacers located on exposed vertical sidewalls of said bottom polysilicon region, said nitride spacers have an outer edge that is aligned with an outer edge of the upper gate conductor region.

15. (Original) The low-resistance T-gate MOSFET of Claim 14 wherein said gate dielectric is an oxide having a dielectric constant of about 3.0 or greater.

16. (Original) The low-resistance T-gate MOSFET of Claim 14 wherein said Si-containing substrate is a component of a silicon-on-insulator wafer.

17. (Original) The low-resistance T-gate MOSFET of Claim 14 wherein said upper gate conductor is composed of polysilicon, a conductive metal, a silicide or a combination thereof.

18. (Original) The low-resistance T-gate MOSFET of Claim 17 wherein said upper gate conductor is composed of a conductive metal.

19. (Original) The low-resistance T-gate MOSFET of Claim 14 wherein said upper gate conductor is composed of W.

20. (Original) The low-resistance T-gate MOSFET of Claim 14 wherein said upper gate conductor is comprised of a conductive stack including W located atop polySi.